



P-Channel 20-V (D-S) MOSFET, Low-Threshold

PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A) ^e	
- 20	0.65 at V _{GS} = - 4.5 V	- 0.58	
	0.85 at V _{GS} = - 2.5 V	- 0.5	

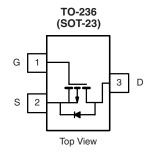
FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET
- ESD Protected: 3000 V



APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- · Battery Operated Systems, DC/DC Converters
- Power Supply Converter Circuits
- · Load/Power Switching-Cell Phones, Pagers



Marking Code: K4ywl

K4 = Part Number Code for TP0101K

y = Year Codew = Week CodeI = Lot Traceability

 $G \longrightarrow 0$

Ordering Information: TP0101K-T1-E3 (Lead (Pb)-free)

TP0101K-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 20	V	
Gate-Source Voltage		V _{GS} ±8		v	
Continuous Drain Current (T, I = 150 °C) ^b	T _A = 25 °C	- I _D	- 0.58		
Continuous Drain Current (1 _J = 150 °C) ²	T _A = 70 °C		- 0.46	A	
Pulsed Drain Current ^a		I _{DM}	- 2		
Continuous Source-Drain (Diode Current) ^b		I _S	- 0.3		
D	T _A = 25 °C	P _D	0.35	W	
Power Dissipation ^b	T _A = 70 °C] 'D	0.22		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

Notes:

- a. Pulse width limited by maximum junction temperature.
- b. Surface Mounted on FR4 board, $t \le 10$ s.

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limits	Unit		
Thermal Resistance, Junction-to-Ambient ^b	R _{thJA}	357	°C/W		

Notes:

- a. Pulse width limited by maximum junction temperature.
- b. Surface Mounted on FR4 board, $t \le 10$ s.

TP0101K

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			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, } I_{D} = -10 \mu\text{A}$	- 20			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -50 \mu A$	- 0.5	- 0.7	- 1.0		
Gate-Body Leakage	I _{GSS}	$V_{DS} = -0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 5	μΑ	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V			- 1		
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C			- 10	1	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 1.2			Δ.	
		$V_{DS} \le -5 \text{ V}, V_{GS} = -2.5 \text{ V}$	- 0.5			Α	
	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 0.58 A		0.42	0.65	0	
Drain-Source On-State Resistance ^a		$V_{GS} = -2.5 \text{ V}, I_D = -0.5 \text{ A}$		0.64	0.85	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 0.58 A		1300		mS	
Diode Forward Voltage ^a	V_{SD}	I _S = - 0.3 A, V _{GS} = 0 V		- 0.9	- 1.2	V	
Dynamic ^b				•	'		
Total Gate Charge	Qg	V 0VV 45V		1400	2200		
Gate-Source Charge	Q _{gs}	$V_{DS} = -6 \text{ V}, V_{GS} = -4.5 \text{ V}$ $I_{D} \cong -0.58 \text{ A}$		300		рC	
Gate-Drain Charge	Q _{gd}	ID = -0.50 A		250			
Gate Resistance	R _g			150		Ω	
Turn On Time	t _{d(on)}			25	35		
Turn-On Time	t _r	V_{DD} = - 6 V, R_L = 10 Ω		30	45		
T 0 " T'	t _{d(off)}	$I_D \cong$ - 0.58 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		55	85	ns	
Turn-Off Time	t _f			38	60		

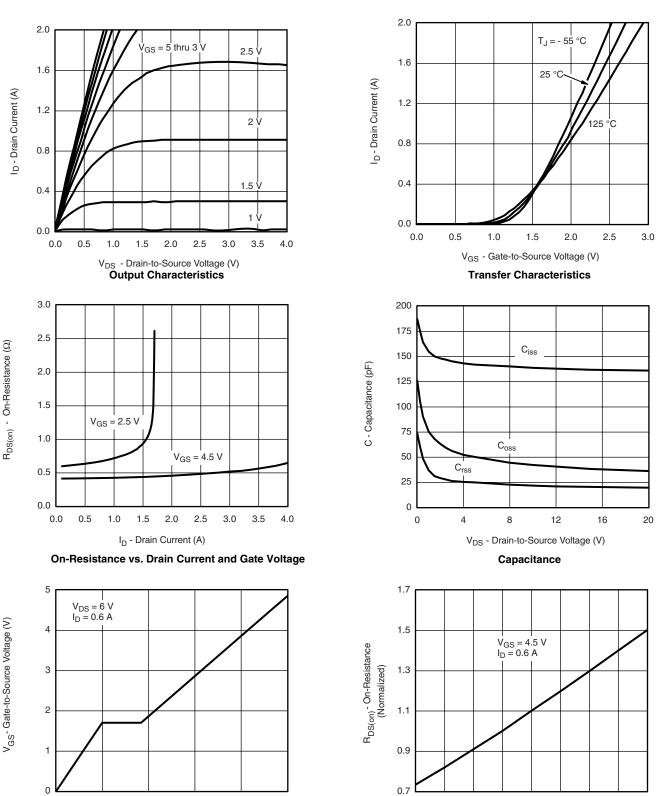
Notes:

- a. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



0.0

0.3

0.6

Q_g - Total Gate Charge (nC)

Gate Charge

0.9

1.2

1.5

- 25

- 50

25

50

T_J - Junction Temperature (°C)

On-Resistance vs. Junction Temperature

75

100

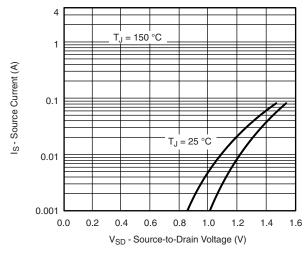
0

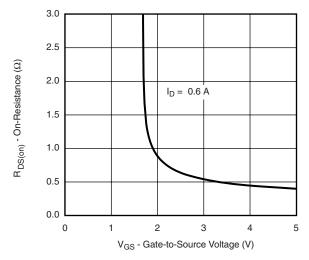
125

150

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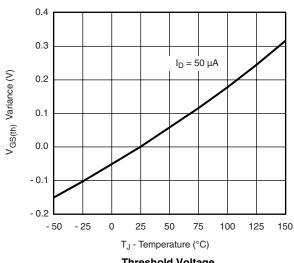
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

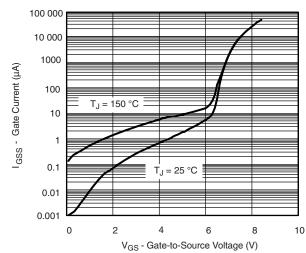




Source-Drain Diode Forward Voltage

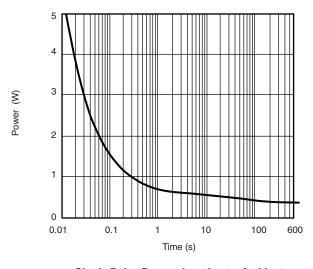
On-Resistance vs. Gate-to-Source Voltage

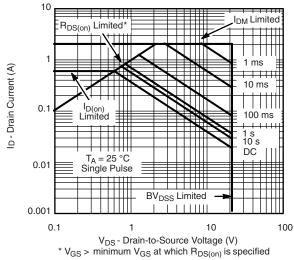




Threshold Voltage

Gate Current vs. Gate-Source Voltage





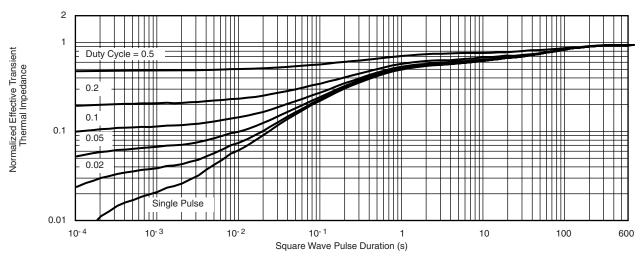
Single Pulse Power, Junction-to-Ambient







TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

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